R&D and Low Volume Manufacturing of Photonic Patterns

Field-test and proven tool for photonics fabrication



PhableR™

- Photolithography system for low volume and R&D.
- Non-contact: protects masks and substrates from damage and contamination
- Highly uniform and reproducible printing
- 1D and 2D periodic pattern printing
- · Suitable for non-flat substrates
- Suitable for thin glass substrates
- High Resolution: <65nm or 125nm (minimum half pitch for UV and DUV versions)
- Overlay alignment capability
- Works with commercially available masks and photoresists
- · Application support: Photoresists, Masks
- Low maintenance and production costs

Applications

ACADEMIC

Nano Optics Nano Materials Plasmonics Research & Development

XR (AR/VR/MR)

Near-Eye Waveguides Head-up Displays (HUD)

OPTOELECTRONICS

DFB/DBR Lasers VCSEL Polarizer Gratings PCSEL Photonic Crystals Nanowire Devices

OPTICAL COMPONENTS

Telecom Gratings Anti-Reflective Surfaces Laser Diffraction Gratings Spectrometer Gratings Wire Grid (Polarizer)

BIO / MEDICAL

Bio Molecular Sensors X-Ray Imaging

COLOR/VISUAL EFFECT

Structural Colors Security Applications



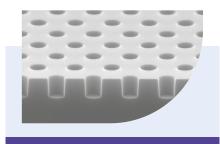
LITHOGRAPHY FOR PHOTONICS



The PhableR tool provides unprecedented ability to print high resolution periodic structures in a low-cost photolithography system. It is similar to a conventional mask-aligner where a photoresist coated wafer is put in proximity to a mask and exposed by a beam of UV light, but thanks to the breakthrough PHABLE exposure technology of Eulitha the resolution is no longer limited by undesired diffraction effects.

Structures such as sub-micron period linear gratings and 2D patterns such as hexagonal and square lattices are printed with high uniformity and fidelity.

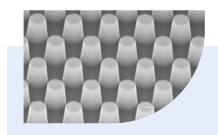
PATTERN EXAMPLES



Hexagonal hole array



Linear grating 300nm pitch



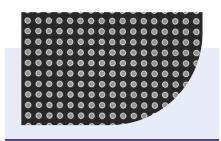
Hexagonal pillar array



Square hole array 350nm pitch



Hexagonal pillar array 3000nm pitch



Square pillar array 300nm pitch

SPECIFICATIONS UV DUV

Resolution (linear grating)	<125nm half-pitch	<65nm half-pitch
Wafer size	100mm, 150mm, larger size on request	
Mask format	5", 6"	
Illumination uniformity	<3%	
Resist thickness	>1µm	>0.1µm
Operation	Manual load – automatic exposure	
Overlay alignment	<1µm frontside, manual	
Beam size	105mm, 155mm, 205mm	